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Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Obsolete
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	36864
Number of I/O	93
Number of Gates	250000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microsemi/m1afs250-2pqg208i

Global Clocking

Fusion devices have extensive support for multiple clocking domains. In addition to the CCC and PLL support described above, there are on-chip oscillators as well as a comprehensive global clock distribution network.

The integrated RC oscillator generates a 100 MHz clock. It is used internally to provide a known clock source to the flash memory read and write control. It can also be used as a source for the PLLs.

The crystal oscillator supports the following operating modes:

- Crystal (32.768 KHz to 20 MHz)
- Ceramic (500 KHz to 8 MHz)
- RC (32.768 KHz to 4 MHz)

Each VersaTile input and output port has access to nine VersaNets: six main and three quadrant global networks. The VersaNets can be driven by the CCC or directly accessed from the core via MUXes. The VersaNets can be used to distribute low-skew clock signals or for rapid distribution of high-fanout nets.

Digital I/Os with Advanced I/O Standards

The Fusion family of FPGAs features a flexible digital I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). Fusion FPGAs support many different digital I/O standards, both single-ended and differential.

The I/Os are organized into banks, with four or five banks per device. The configuration of these banks determines the I/O standards supported. The banks along the east and west sides of the device support the full range of I/O standards (single-ended and differential). The south bank supports the Analog Quads (analog I/O). In the family's two smaller devices, the north bank supports multiple single-ended digital I/O standards. In the family's larger devices, the north bank is divided into two banks of digital Pro I/Os, supporting a wide variety of single-ended, differential, and voltage-referenced I/O standards.

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following applications:

- Single-Data-Rate (SDR) applications
- Double-Data-Rate (DDR) applications—DDR LVDS I/O for chip-to-chip communications
- Fusion banks support LVPECL, LVDS, BLVDS, and M-LVDS with 20 multi-drop points.

VersaTiles

The Fusion core consists of VersaTiles, which are also used in the successful ProASIC3 family. The Fusion VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set and optional enable

Refer to [Figure 1-2](#) for the VersaTile configuration arrangement.

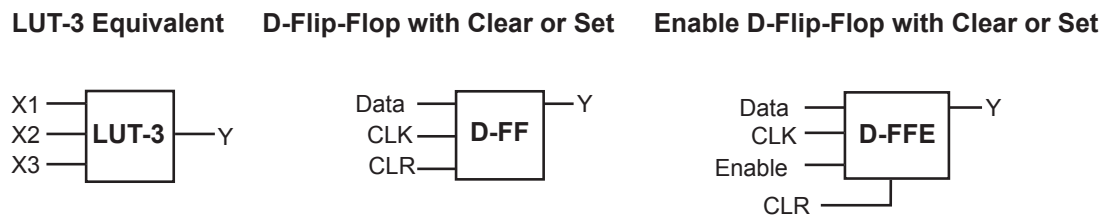


Figure 1-2 • VersaTile Configurations

CCC and PLL Characteristics

Timing Characteristics

Table 2-12 • Fusion CCC/PLL Specification

Parameter	Min.	Typ.	Max.	Unit
Clock Conditioning Circuitry Input Frequency f_{IN_CCC}	1.5		350	MHz
Clock Conditioning Circuitry Output Frequency f_{OUT_CCC}	0.75		350	MHz
Delay Increments in Programmable Delay Blocks ^{1, 2}		160 ³		ps
Number of Programmable Values in Each Programmable Delay Block			32	
Input Period Jitter			1.5	ns
CCC Output Peak-to-Peak Period Jitter F_{CCC_OUT}	Max Peak-to-Peak Period Jitter			
	1 Global Network Used		3 Global Networks Used	
0.75 MHz to 24 MHz	1.00%		1.00%	
24 MHz to 100 MHz	1.50%		1.50%	
100 MHz to 250 MHz	2.25%		2.25%	
250 MHz to 350 MHz	3.50%		3.50%	
Acquisition Time	LockControl = 0		300	μs
	LockControl = 1		6.0	ms
Tracking Jitter ⁴	LockControl = 0		1.6	ns
	LockControl = 1		0.8	ns
Output Duty Cycle	48.5		51.5	%
Delay Range in Block: Programmable Delay 1 ^{1, 2}	0.6		5.56	ns
Delay Range in Block: Programmable Delay 2 ^{1, 2}	0.025		5.56	ns
Delay Range in Block: Fixed Delay ^{1, 2}		2.2		ns

Notes:

1. This delay is a function of voltage and temperature. See [Table 3-7 on page 3-9](#) for deratings.
2. $T_J = 25^\circ\text{C}$, $V_{CC} = 1.5\text{ V}$
3. When the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available. Refer to the Libero SoC Online Help associated with the core for more information.
4. Tracking jitter is defined as the variation in clock edge position of PLL outputs with reference to PLL input clock edge. Tracking jitter does not measure the variation in PLL output period, which is covered by period jitter parameter.

Data operations are performed in widths of 1 to 4 bytes. A write to a location in a page that is not already in the Page Buffer will cause the page to be read from the FB Array and stored in the Page Buffer. The block that was addressed during the write will be put into the Block Buffer, and the data written by WD will overwrite the data in the Block Buffer. After the data is written to the Block Buffer, the Block Buffer is then written to the Page Buffer to keep both buffers in sync. Subsequent writes to the same block will overwrite the Block Buffer and the Page Buffer. A write to another block in the page will cause the addressed block to be loaded from the Page Buffer, and the write will be performed as described previously.

The data width can be selected dynamically via the DATAWIDTH input bus. The truth table for the data width settings is detailed in [Table 2-21](#). The minimum resolvable address is one 8-bit byte. For data widths greater than 8 bits, the corresponding address bits are ignored—when DATAWIDTH = 0 (2 bytes), ADDR[0] is ignored, and when DATAWIDTH = '10' or '11' (4 bytes), ADDR[1:0] are ignored. Data pins are LSB-oriented and unused WD data pins must be grounded.

Table 2-21 • Data Width Settings

DATAWIDTH[1:0]	Data Width
00	1 byte [7:0]
01	2 byte [15:0]
10, 11	4 bytes [31:0]

Flash Memory Block Protection

Page Loss Protection

When the PAGELOSSPROTECT pin is set to logic 1, it prevents writes to any page other than the current page in the Page Buffer until the page is either discarded or programmed.

A write to another page while the current page is Page Loss Protected will return a STATUS of '11'.

Overwrite Protection

Any page that is Overwrite Protected will result in the STATUS being set to '01' when an attempt is made to either write, program, or erase it. To set the Overwrite Protection state for a page, set the OVERWRITEPROTECT pin when a Program operation is undertaken. To clear the Overwrite Protect state for a given page, an Unprotect Page operation must be performed on the page, and then the page must be programmed with the OVERWRITEPROTECT pin cleared to save the new page.

LOCKREQUEST

The LOCKREQUEST signal is used to give the user interface control over simultaneous access of the FB from both the User and JTAG interfaces. When LOCKREQUEST is asserted, the JTAG interface will hold off any access attempts until LOCKREQUEST is deasserted.

Flash Memory Block Operations

FB Operation Priority

The FB provides for priority of operations when multiple actions are requested simultaneously. [Table 2-22](#) shows the priority order (priority 0 is the highest).

Table 2-22 • FB Operation Priority

Operation	Priority
System Initialization	0
FB Reset	1
Read	2
Write	3
Erase Page	4
Program	5
Unprotect Page	6
Discard Page	7

DINA and DINB

These are the input data signals, and they are nine bits wide. Not all nine bits are valid in all configurations. When a data width less than nine is specified, unused high-order signals must be grounded ([Table 2-29](#)).

DOUTA and DOUTB

These are the nine-bit output data signals. Not all nine bits are valid in all configurations. As with DINA and DINB, high-order bits may not be used ([Table 2-29](#)). The output data on unused pins is undefined.

Table 2-29 • Unused/Used Input and Output Data Pins for Various Supported Bus Widths

D×W	DINx/DOUTx	
	Unused	Used
4k×1	[8:1]	[0]
2k×2	[8:2]	[1:0]
1k×4	[8:4]	[3:0]
512×9	None	[8:0]

Note: The "x" in DINx and DOUTx implies A or B.

The rate at which the gate voltage of the external MOSFET slews is determined by the current, I_g , sourced or sunk by the AG pin and the gate-to-source capacitance, C_{GS} , of the external MOSFET. As an approximation, the slew rate is given by [EQ 6](#).

$$dv/dt = I_g / C_{GS}$$

EQ 6

C_{GS} is not a fixed capacitance but, depending on the circuitry connected to its drain terminal, can vary significantly during the course of a turn-on or turn-off transient. Thus, [EQ 6 on page 2-91](#) can only be used for a first-order estimate of the switching speed of the external MOSFET.

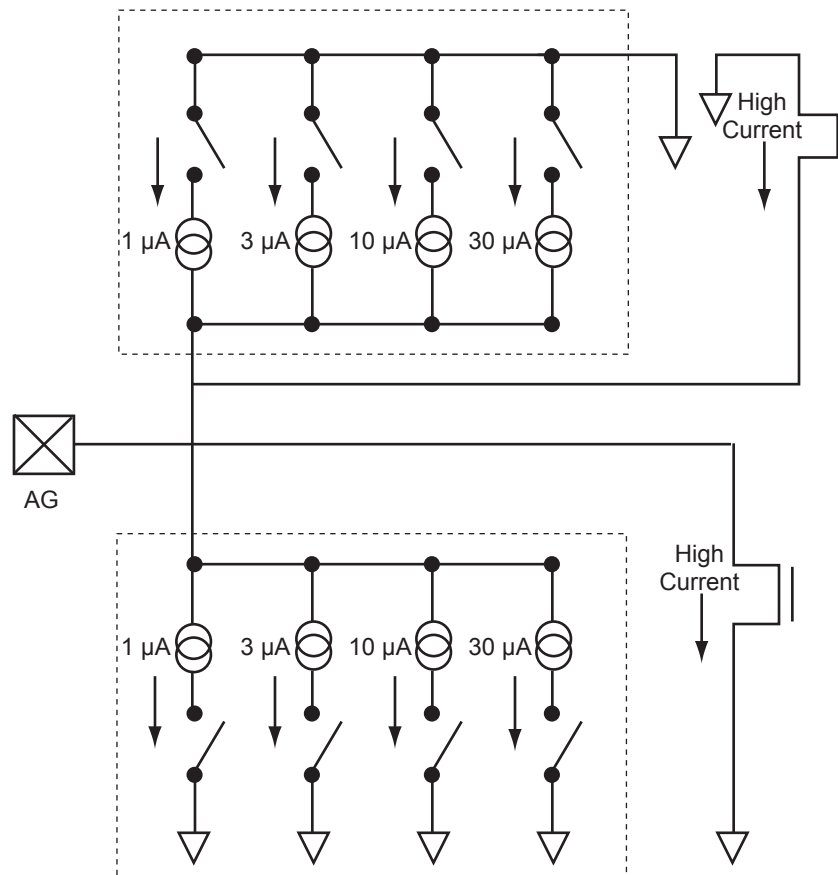


Figure 2-75 • Gate Driver Example

Offset Error

Offset error indicates how well the actual transfer function matches the ideal transfer function at a single point. For an ideal ADC, the first transition occurs at 0.5 LSB above zero. The offset voltage is measured by applying an analog input such that the ADC outputs all zeroes and increases until the first transition occurs (Figure 2-86).

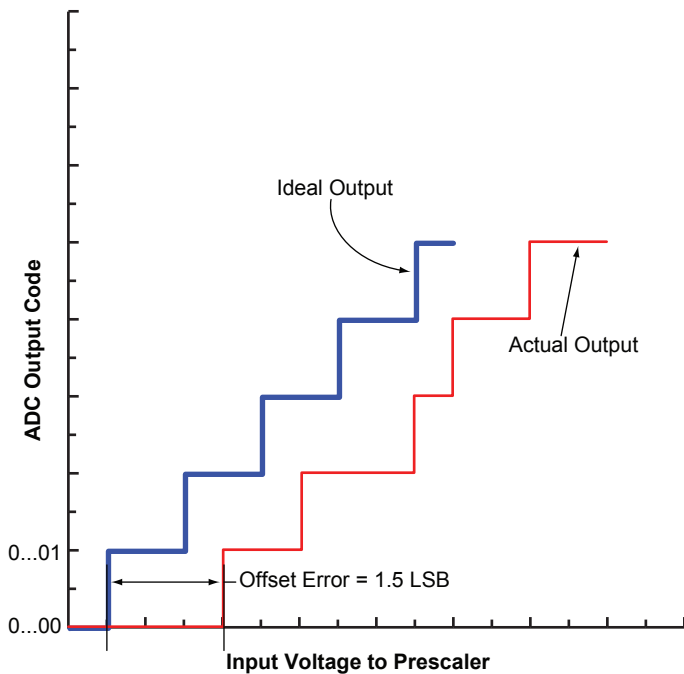


Figure 2-86 • Offset Error

Resolution

ADC resolution is the number of bits used to represent an analog input signal. To more accurately replicate the analog signal, resolution needs to be increased.

Sampling Rate

Sampling rate or sample frequency, specified in samples per second (sps), is the rate at which an ADC acquires (samples) the analog input.

SNR – Signal-to-Noise Ratio

SNR is the ratio of the amplitude of the desired signal to the amplitude of the noise signals at a given point in time. For a waveform perfectly reconstructed from digital samples, the theoretical maximum SNR (EQ 14) is the ratio of the full-scale analog input (RMS value) to the RMS quantization error (residual error). The ideal, theoretical minimum ADC noise is caused by quantization error only and results directly from the ADC's resolution (N bits):

$$SNR_{dB[Max]} = 6.02_{dB} \times N + 1.76_{dB}$$

EQ 14

SINAD – Signal-to-Noise and Distortion

SINAD is the ratio of the rms amplitude to the mean value of the root-sum-square of the all other spectral components, including harmonics, but excluding DC. SINAD is a good indication of the overall dynamic performance of an ADC because it includes all components which make up noise and distortion.

Total Harmonic Distortion

THD measures the distortion content of a signal, and is specified in decibels relative to the carrier (dBc). THD is the ratio of the RMS sum of the selected harmonics of the input signal to the fundamental itself. Only harmonics within the Nyquist limit are included in the measurement.

ADC Interface Timing

Table 2-48 • ADC Interface Timing
 Commercial Temperature Range Conditions: $T_J = 70^{\circ}\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{SUMODE}	Mode Pin Setup Time	0.56	0.64	0.75	ns
t_{HDMODE}	Mode Pin Hold Time	0.26	0.29	0.34	ns
t_{SUTVC}	Clock Divide Control (TVC) Setup Time	0.68	0.77	0.90	ns
t_{HDTVC}	Clock Divide Control (TVC) Hold Time	0.32	0.36	0.43	ns
t_{SUSTC}	Sample Time Control (STC) Setup Time	1.58	1.79	2.11	ns
t_{HDSTC}	Sample Time Control (STC) Hold Time	1.27	1.45	1.71	ns
$t_{\text{SUVAREFSEL}}$	Voltage Reference Select (VAREFSEL) Setup Time	0.00	0.00	0.00	ns
$t_{\text{HDVAREFSEL}}$	Voltage Reference Select (VAREFSEL) Hold Time	0.67	0.76	0.89	ns
t_{SUCHNUM}	Channel Select (CHNUMBER) Setup Time	0.90	1.03	1.21	ns
t_{HDCHNUM}	Channel Select (CHNUMBER) Hold Time	0.00	0.00	0.00	ns
$t_{\text{SUADCSTART}}$	Start of Conversion (ADCSTART) Setup Time	0.75	0.85	1.00	ns
$t_{\text{HDADCSTART}}$	Start of Conversion (ADCSTART) Hold Time	0.43	0.49	0.57	ns
t_{CK2QBUSY}	Busy Clock-to-Q	1.33	1.51	1.78	ns
t_{CK2QCAL}	Power-Up Calibration Clock-to-Q	0.63	0.71	0.84	ns
t_{CK2QVAL}	Valid Conversion Result Clock-to-Q	3.12	3.55	4.17	ns
$t_{\text{CK2QSAMPLE}}$	Sample Clock-to-Q	0.22	0.25	0.30	ns
$t_{\text{CK2QRESULT}}$	Conversion Result Clock-to-Q	2.53	2.89	3.39	ns
$t_{\text{CLR2QBUSY}}$	Busy Clear-to-Q	2.06	2.35	2.76	ns
t_{CLR2QCAL}	Power-Up Calibration Clear-to-Q	2.15	2.45	2.88	ns
t_{CLR2QVAL}	Valid Conversion Result Clear-to-Q	2.41	2.74	3.22	ns
$t_{\text{CLR2QSAMPLE}}$	Sample Clear-to-Q	2.17	2.48	2.91	ns
$t_{\text{CLR2QRESULT}}$	Conversion result Clear-to-Q	2.25	2.56	3.01	ns
t_{RECCLR}	Recovery Time of Clear	0.00	0.00	0.00	ns
t_{REMCLR}	Removal Time of Clear	0.63	0.72	0.84	ns
$t_{\text{MPWSYSCLK}}$	Clock Minimum Pulse Width for the ADC	4.00	4.00	4.00	ns
$t_{\text{FMAXSYSCLK}}$	Clock Maximum Frequency for the ADC	100.00	100.00	100.00	MHz

Table 2-49 • Analog Channel Specifications (continued)
Commercial Temperature Range Conditions, $T_J = 85^\circ\text{C}$ (unless noted otherwise),
Typical: $V_{CC33A} = 3.3\text{ V}$, $V_{CC} = 1.5\text{ V}$

Parameter	Description	Condition	Min.	Typ.	Max.	Units
Temperature Monitor Using Analog Pad AT						
External Temperature Monitor (external diode 2N3904, $T_J = 25^\circ\text{C}$) ⁴	Resolution	8-bit ADC		4		$^\circ\text{C}$
		10-bit ADC		1		$^\circ\text{C}$
		12-bit ADC		0.25		$^\circ\text{C}$
	Systematic Offset ⁵	AFS090, AFS250, AFS600, AFS1500, uncalibrated ⁷		5		$^\circ\text{C}$
		AFS090, AFS250, AFS600, AFS1500, calibrated ⁷		± 5		$^\circ\text{C}$
	Accuracy			± 3	± 5	$^\circ\text{C}$
	External Sensor Source Current	High level, TMSTBx = 0		10		μA
		Low level, TMSTBx = 1		100		μA
	Max Capacitance on AT pad				1.3	nF
Internal Temperature Monitor	Resolution	8-bit ADC	4			$^\circ\text{C}$
		10-bit ADC	1			$^\circ\text{C}$
		12-bit ADC	0.25			$^\circ\text{C}$
	Systematic Offset ⁵	AFS090 ⁷		5		$^\circ\text{C}$
		AFS250, AFS600, AFS1500 ⁷		11		$^\circ\text{C}$
	Accuracy			± 3	± 5	$^\circ\text{C}$
t_{TMSHI}	Strobe High time		10		105	μs
t_{TMSLO}	Strobe Low time		5			μs
t_{TMSSET}	Settling time		5			μs

Notes:

1. V_{RSM} is the maximum voltage drop across the current sense resistor.
2. Analog inputs used as digital inputs can tolerate the same voltage limits as the corresponding analog pad. There is no reliability concern on digital inputs as long as V_{IND} does not exceed these limits.
3. V_{IND} is limited to $V_{\text{CC33A}} + 0.2$ to allow reaching 10 MHz input frequency.
4. An averaging of 1,024 samples (LPF setting in Analog System Builder) is required and the maximum capacitance allowed across the AT pins is 500 pF.
5. The temperature offset is a fixed positive value.
6. The high current mode has a maximum power limit of 20 mW. Appropriate current limit resistors must be used, based on voltage on the pad.
7. When using SmartGen Analog System Builder, CalibIP is required to obtain specified offset. For further details on CalibIP, refer to the "Temperature, Voltage, and Current Calibration in Fusion FPGAs" chapter of the [Fusion FPGA Fabric User Guide](#).

User I/Os

Introduction

Fusion devices feature a flexible I/O structure, supporting a range of mixed voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V) through a bank-selectable voltage. [Table 2-68](#), [Table 2-69](#), [Table 2-70](#), and [Table 2-71 on page 2-135](#) show the voltages and the compatible I/O standards. I/Os provide programmable slew rates, drive strengths, weak pull-up, and weak pull-down circuits. 3.3 V PCI and 3.3 V PCI-X are 5 V-tolerant. See the ["5 V Input Tolerance" section on page 2-144](#) for possible implementations of 5 V tolerance.

All I/Os are in a known state during power-up, and any power-up sequence is allowed without current impact. Refer to the ["I/O Power-Up and Supply Voltage Thresholds for Power-On Reset \(Commercial and Industrial\)" section on page 3-5](#) for more information. In low power standby or sleep mode (VCC is OFF, VCC33A is ON, VCCI is ON) or when the resource is not used, digital inputs are tristated, digital outputs are tristated, and digital bibufs (input/output) are tristated.

I/O Tile

The Fusion I/O tile provides a flexible, programmable structure for implementing a large number of I/O standards. In addition, the registers available in the I/O tile in selected I/O banks can be used to support high-performance register inputs and outputs, with register enable if desired ([Figure 2-99 on page 2-133](#)). The registers can also be used to support the JESD-79C DDR standard within the I/O structure (see the ["Double Data Rate \(DDR\) Support" section on page 2-139](#) for more information).

As depicted in [Figure 2-100 on page 2-138](#), all I/O registers share one CLR port. The output register and output enable register share one CLK port. Refer to the ["I/O Registers" section on page 2-138](#) for more information.

I/O Banks and I/O Standards Compatibility

The digital I/Os are grouped into I/O voltage banks. There are three digital I/O banks on the AFS090 and AFS250 devices and four digital I/O banks on the AFS600 and AFS1500 devices. [Figure 2-113 on page 2-158](#) and [Figure 2-114 on page 2-159](#) show the bank configuration by device. The north side of the I/O in the AFS600 and AFS1500 devices comprises two banks of Pro I/Os. The Pro I/Os support a wide number of voltage-referenced I/O standards in addition to the multitude of single-ended and differential I/O standards common throughout all Microsemi digital I/Os. Each I/O voltage bank has dedicated I/O supply and ground voltages (VCCI/GNDQ for input buffers and VCCI/GND for output buffers). Because of these dedicated supplies, only I/Os with compatible standards can be assigned to the same I/O voltage bank. [Table 2-69](#) and [Table 2-70 on page 2-134](#) show the required voltage compatibility values for each of these voltages.

For more information about I/O and global assignments to I/O banks, refer to the specific pin table of the device in the ["Package Pin Assignments" on page 4-1](#) and the ["User I/O Naming Convention" section on page 2-158](#).

Each Pro I/O bank is divided into minibanks. Any user I/O in a VREF minibank (a minibank is the region of scope of a VREF pin) can be configured as a VREF pin ([Figure 2-99 on page 2-133](#)). Only one VREF pin is needed to control the entire VREF minibank. The location and scope of the VREF minibanks can be determined by the I/O name. For details, see the ["User I/O Naming Convention" section on page 2-158](#).

[Table 2-70 on page 2-134](#) shows the I/O standards supported by Fusion devices and the corresponding voltage levels.

I/O standards are compatible if the following are true:

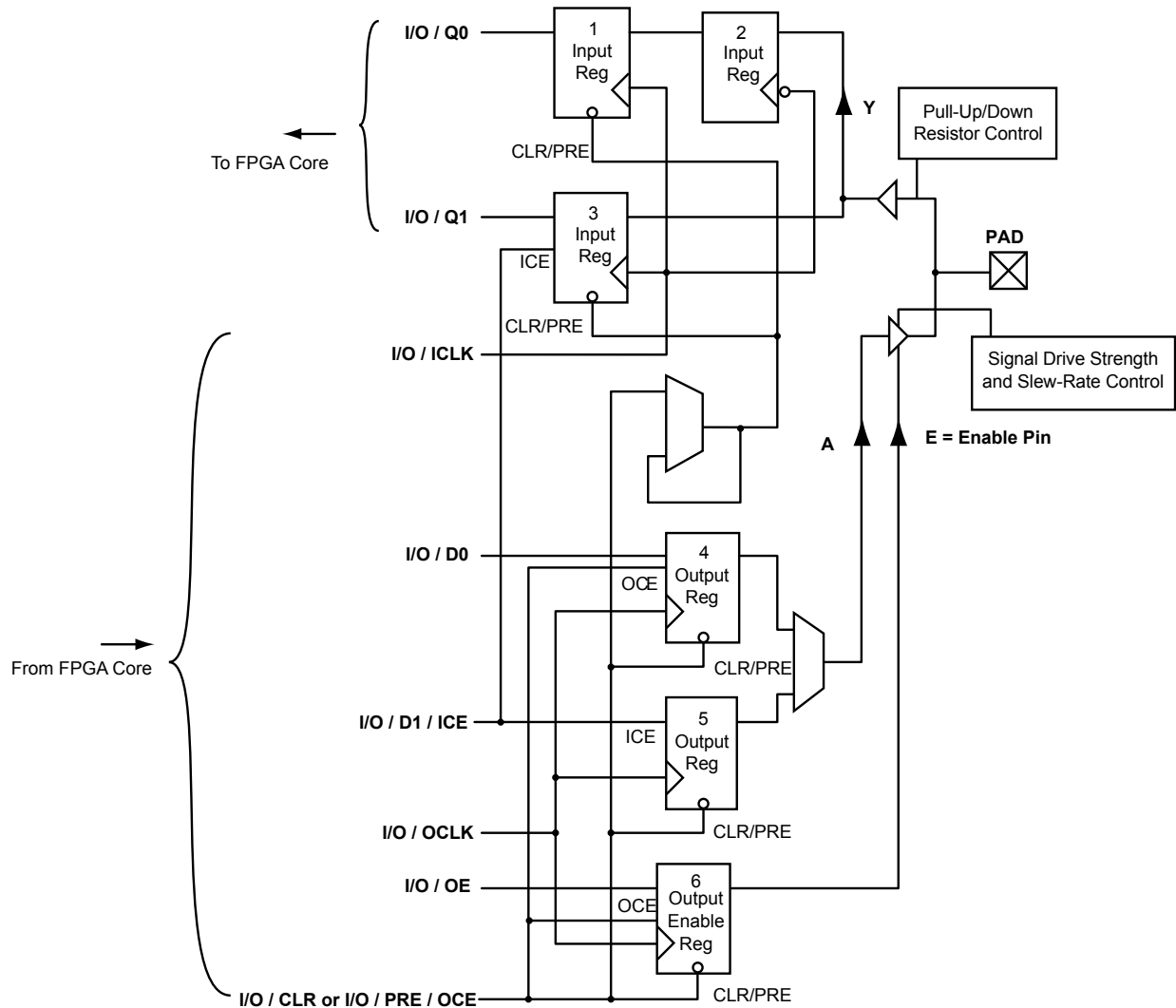
- Their VCCI values are identical.
- If both of the standards need a VREF, their VREF values must be identical (Pro I/O only).

I/O Registers

Each I/O module contains several input, output, and enable registers. Refer to Figure 2-100 for a simplified representation of the I/O block.

The number of input registers is selected by a set of switches (not shown in Figure 2-100) between registers to implement single or differential data transmission to and from the FPGA core. The Designer software sets these switches for the user.

A common CLR/PRE signal is employed by all I/O registers when I/O register combining is used. Input register 2 does not have a CLR/PRE pin, as this register is used for DDR implementation. The I/O register combining must satisfy some rules.



Note: Fusion I/Os have registers to support DDR functionality (see the "Double Data Rate (DDR) Support" section on page 2-139 for more information).

Figure 2-100 • I/O Block Logical Representation

5 V Input Tolerance

I/Os can support 5 V input tolerance when LVTTTL 3.3 V, LVCMOS 3.3 V, LVCMOS 2.5 V / 5 V, and LVCMOS 2.5 V configurations are used (see [Table 2-77 on page 2-147](#) for more details). There are four recommended solutions (see [Figure 2-103 to Figure 2-106 on page 2-146](#) for details of board and macro setups) to achieve 5 V receiver tolerance. All the solutions meet a common requirement of limiting the voltage at the input to 3.6 V or less. In fact, the I/O absolute maximum voltage rating is 3.6 V, and any voltage above 3.6 V may cause long-term gate oxide failures.

Solution 1

The board-level design needs to ensure that the reflected waveform at the pad does not exceed the limits provided in [Table 3-4 on page 3-4](#). This is a long-term reliability requirement.

This scheme will also work for a 3.3 V PCI / PCI-X configuration, but the internal diode should not be used for clamping, and the voltage must be limited by the two external resistors, as explained below. Relying on the diode clamping would create an excessive pad DC voltage of $3.3\text{ V} + 0.7\text{ V} = 4\text{ V}$.

The following are some examples of possible resistor values (based on a simplified simulation model with no line effects and $10\ \Omega$ transmitter output resistance, where $R_{tx_out_high} = (V_{CCI} - V_{OH}) / I_{OH}$, $R_{tx_out_low} = V_{OL} / I_{OL}$).

Example 1 (high speed, high current):

$R_{tx_out_high} = R_{tx_out_low} = 10\ \Omega$

$R1 = 36\ \Omega (\pm 5\%), P(r1)_{min} = 0.069\ \Omega$

$R2 = 82\ \Omega (\pm 5\%), P(r2)_{min} = 0.158\ \Omega$

$I_{max_tx} = 5.5\text{ V} / (82 * 0.95 + 36 * 0.95 + 10) = 45.04\text{ mA}$

$t_{RISE} = t_{FALL} = 0.85\text{ ns}$ at $C_{pad_load} = 10\text{ pF}$ (includes up to 25% safety margin)

$t_{RISE} = t_{FALL} = 4\text{ ns}$ at $C_{pad_load} = 50\text{ pF}$ (includes up to 25% safety margin)

Example 2 (low-medium speed, medium current):

$R_{tx_out_high} = R_{tx_out_low} = 10\ \Omega$

$R1 = 220\ \Omega (\pm 5\%), P(r1)_{min} = 0.018\ \Omega$

$R2 = 390\ \Omega (\pm 5\%), P(r2)_{min} = 0.032\ \Omega$

$I_{max_tx} = 5.5\text{ V} / (220 * 0.95 + 390 * 0.95 + 10) = 9.17\text{ mA}$

$t_{RISE} = t_{FALL} = 4\text{ ns}$ at $C_{pad_load} = 10\text{ pF}$ (includes up to 25% safety margin)

$t_{RISE} = t_{FALL} = 20\text{ ns}$ at $C_{pad_load} = 50\text{ pF}$ (includes up to 25% safety margin)

Other values of resistors are also allowed as long as the resistors are sized appropriately to limit the voltage at the receiving end to $2.5\text{ V} < V_{in(rx)} < 3.6\text{ V}$ when the transmitter sends a logic 1. This range of $V_{in_dc(rx)}$ must be assured for any combination of transmitter supply ($5\text{ V} \pm 0.5\text{ V}$), transmitter output resistance, and board resistor tolerances.

Table 2-107 • 3.3 V LVTTTL / 3.3 V LVCMOS High Slew

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Advanced I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
4 mA	Std.	0.66	7.66	0.04	1.20	0.43	7.80	6.59	2.65	2.61	10.03	8.82	ns
	–1	0.56	6.51	0.04	1.02	0.36	6.63	5.60	2.25	2.22	8.54	7.51	ns
	–2	0.49	5.72	0.03	0.90	0.32	5.82	4.92	1.98	1.95	7.49	6.59	ns
8 mA	Std.	0.66	4.91	0.04	1.20	0.43	5.00	4.07	2.99	3.20	7.23	6.31	ns
	–1	0.56	4.17	0.04	1.02	0.36	4.25	3.46	2.54	2.73	6.15	5.36	ns
	–2	0.49	3.66	0.03	0.90	0.32	3.73	3.04	2.23	2.39	5.40	4.71	ns
12 mA	Std.	0.66	3.53	0.04	1.20	0.43	3.60	2.82	3.21	3.58	5.83	5.06	ns
	–1	0.56	3.00	0.04	1.02	0.36	3.06	2.40	2.73	3.05	4.96	4.30	ns
	–2	0.49	2.64	0.03	0.90	0.32	2.69	2.11	2.40	2.68	4.36	3.78	ns
16 mA	Std.	0.66	3.33	0.04	1.20	0.43	3.39	2.56	3.26	3.68	5.63	4.80	ns
	–1	0.56	2.83	0.04	1.02	0.36	2.89	2.18	2.77	3.13	4.79	4.08	ns
	–2	0.49	2.49	0.03	0.90	0.32	2.53	1.91	2.44	2.75	4.20	3.58	ns
24 mA	Std.	0.66	3.08	0.04	1.20	0.43	3.13	2.12	3.32	4.06	5.37	4.35	ns
	–1	0.56	2.62	0.04	1.02	0.36	2.66	1.80	2.83	3.45	4.57	3.70	ns
	–2	0.49	2.30	0.03	0.90	0.32	2.34	1.58	2.48	3.03	4.01	3.25	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

Table 2-108 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$,
Worst-Case $V_{CCI} = 3.0\text{ V}$
Applicable to Standard I/Os

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
4 mA	Std.	0.66	9.46	0.04	1.00	0.43	9.64	8.54	2.07	2.04	ns
	–1	0.56	8.05	0.04	0.85	0.36	8.20	7.27	1.76	1.73	ns
	–2	0.49	7.07	0.03	0.75	0.32	7.20	6.38	1.55	1.52	ns
6 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns
8 mA	Std.	0.66	6.57	0.04	1.00	0.43	6.69	5.98	2.40	2.57	ns
	–1	0.56	5.59	0.04	0.85	0.36	5.69	5.09	2.04	2.19	ns
	–2	0.49	4.91	0.03	0.75	0.32	5.00	4.47	1.79	1.92	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to [Table 3-7 on page 3-9](#).

VCC Core Supply Voltage

Supply voltage to the FPGA core, nominally 1.5 V. VCC is also required for powering the JTAG state machine, in addition to VJTAG. Even when a Fusion device is in bypass mode in a JTAG chain of interconnected devices, both VCC and VJTAG must remain powered to allow JTAG signals to pass through the Fusion device.

VCCIBx I/O Supply Voltage

Supply voltage to the bank's I/O output buffers and I/O logic. Bx is the I/O bank number. There are either four (AFS090 and AFS250) or five (AFS600 and AFS1500) I/O banks on the Fusion devices plus a dedicated VJTAG bank.

Each bank can have a separate VCCI connection. All I/Os in a bank will run off the same VCCIBx supply. VCCI can be 1.5 V, 1.8 V, 2.5 V, or 3.3 V, nominal voltage. Unused I/O banks should have their corresponding VCCI pins tied to GND.

VCCPLA/B PLL Supply Voltage

Supply voltage to analog PLL, nominally 1.5 V, where A and B refer to the PLL. AFS090 and AFS250 each have a single PLL. The AFS600 and AFS1500 devices each have two PLLs. Microsemi recommends tying VCCPLX to VCC and using proper filtering circuits to decouple VCC noise from PLL. If unused, VCCPLA/B should be tied to GND.

VCOMPLA/B Ground for West and East PLL

VCOMPLA is the ground of the west PLL (CCC location F) and VCOMPLB is the ground of the east PLL (CCC location C).

VJTAG JTAG Supply Voltage

Fusion devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned to be used, the VJTAG pin together with the TRST pin could be tied to GND. It should be noted that VCC is required to be powered for JTAG operation; VJTAG alone is insufficient. If a Fusion device is in a JTAG chain of interconnected boards and it is desired to power down the board containing the Fusion device, this may be done provided both VJTAG and VCC to the Fusion part remain powered; otherwise, JTAG signals will not be able to transition the Fusion device, even in bypass mode.

VPUMP Programming Supply Voltage

Fusion devices support single-voltage ISP programming of the configuration flash and FlashROM. For programming, VPUMP should be in the 3.3 V +/-5% range. During normal device operation, VPUMP can be left floating or can be tied to any voltage between 0 V and 3.6 V.

When the VPUMP pin is tied to ground, it shuts off the charge pump circuitry, resulting in no sources of oscillation from the charge pump circuitry.

For proper programming, 0.01 μ F and 0.33 μ F capacitors (both rated at 16 V) are to be connected in parallel across VPUMP and GND, and positioned as close to the FPGA pins as possible.

IEEE 1532 Characteristics

JTAG timing delays do not include JTAG I/Os. To obtain complete JTAG timing, add I/O buffer delays to the corresponding standard selected; refer to the I/O timing characteristics in the "User I/Os" section on page 2-132 for more details.

Timing Characteristics

Table 2-186 • JTAG 1532

Commercial Temperature Range Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
t_{DISU}	Test Data Input Setup Time	0.50	0.57	0.67	ns
t_{DIHD}	Test Data Input Hold Time	1.00	1.13	1.33	ns
t_{TMSSU}	Test Mode Select Setup Time	0.50	0.57	0.67	ns
t_{TMDHD}	Test Mode Select Hold Time	1.00	1.13	1.33	ns
t_{TCK2Q}	Clock to Q (data out)	6.00	6.80	8.00	ns
t_{RSTB2Q}	Reset to Q (data out)	20.00	22.67	26.67	ns
F_{TCKMAX}	TCK Maximum Frequency	25.00	22.00	19.00	MHz
$t_{TRSTREM}$	ResetB Removal Time	0.00	0.00	0.00	ns
$t_{TRSTREC}$	ResetB Recovery Time	0.20	0.23	0.27	ns
$t_{TRSTMPW}$	ResetB Minimum Pulse	TBD	TBD	TBD	ns

Note: For the derating values at specific junction temperature and voltage supply levels, refer to Table 3-7 on page 3-9.

3 – DC and Power Characteristics

General Specifications

Operating Conditions

Stresses beyond those listed in [Table 3-1](#) may cause permanent damage to the device.

Exposure to absolute maximum rated conditions for extended periods may affect device reliability. Devices should not be operated outside the recommended operating ranges specified in [Table 3-2](#) on [page 3-3](#).

Table 3-1 • Absolute Maximum Ratings

Symbol	Parameter	Commercial	Industrial	Units
VCC	DC core supply voltage	–0.3 to 1.65	–0.3 to 1.65	V
VJTAG	JTAG DC voltage	–0.3 to 3.75	–0.3 to 3.75	V
VPUMP	Programming voltage	–0.3 to 3.75	–0.3 to 3.75	V
VCCPLL	Analog power supply (PLL)	–0.3 to 1.65	–0.3 to 1.65	V
VCCI	DC I/O output buffer supply voltage	–0.3 to 3.75	–0.3 to 3.75	V
VI	I/O input voltage ¹	–0.3 V to 3.6 V (when I/O hot insertion mode is enabled) –0.3 V to (VCCI + 1 V) or 3.6 V, whichever voltage is lower (when I/O hot-insertion mode is disabled)		V
VCC33A	+3.3 V power supply	–0.3 to 3.75 ²	–0.3 to 3.75 ²	V
VCC33PMP	+3.3 V power supply	–0.3 to 3.75 ²	–0.3 to 3.75 ²	V
VAREF	Voltage reference for ADC	–0.3 to 3.75	–0.3 to 3.75	V
VCC15A	Digital power supply for the analog system	–0.3 to 1.65	–0.3 to 1.65	V
VCCNVM	Embedded flash power supply	–0.3 to 1.65	–0.3 to 1.65	V
VCCOSC	Oscillator power supply	–0.3 to 3.75	–0.3 to 3.75	V

Notes:

1. The device should be operated within the limits specified by the datasheet. During transitions, the input signal may undershoot or overshoot according to the limits shown in [Table 3-4](#) on [page 3-4](#).
2. Analog data not valid beyond 3.65 V.
3. The high current mode has a maximum power limit of 20 mW. Appropriate current limit resistors must be used, based on voltage on the pad.
4. For flash programming and retention maximum limits, refer to [Table 3-5](#) on [page 3-5](#). For recommended operating limits refer to [Table 3-2](#) on [page 3-3](#).

Table 3-8 • AFS1500 Quiescent Supply Current Characteristics (continued)

Parameter	Description	Conditions	Temp.	Min.	Typ.	Max.	Unit
IJTAG	JTAG I/O quiescent current	Operational standby ⁴ , VJTAG = 3.63 V	T _J = 25°C		80	100	μA
			T _J = 85°C		80	100	μA
			T _J = 100°C		80	100	μA
		Standby mode ⁵ or Sleep mode ⁶ , VJTAG = 0 V			0	0	μA
IPP	Programming supply current	Non-programming mode, VPUMP = 3.63 V	T _J = 25°C		39	80	μA
			T _J = 85°C		40	80	μA
			T _J = 100°C		40	80	μA
		Standby mode ⁵ or Sleep mode ⁶ , VPUMP = 0 V			0	0	μA
ICCNVM	Embedded NVM current	Reset asserted, V _{CCNVM} = 1.575 V	T _J = 25°C		50	150	μA
			T _J = 85°C		50	150	μA
			T _J = 100°C		50	150	μA
ICCPLL	1.5 V PLL quiescent current	Operational standby , VCCPLL = 1.575 V	T _J = 25°C		130	200	μA
			T _J = 85°C		130	200	μA
			T _J = 100°C		130	200	μA

Notes:

1. ICC is the 1.5 V power supplies, ICC and ICC15A.
2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.
3. ICCI includes all ICCI0, ICCI1, ICCI2, and ICCI4.
4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.
5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.
6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.

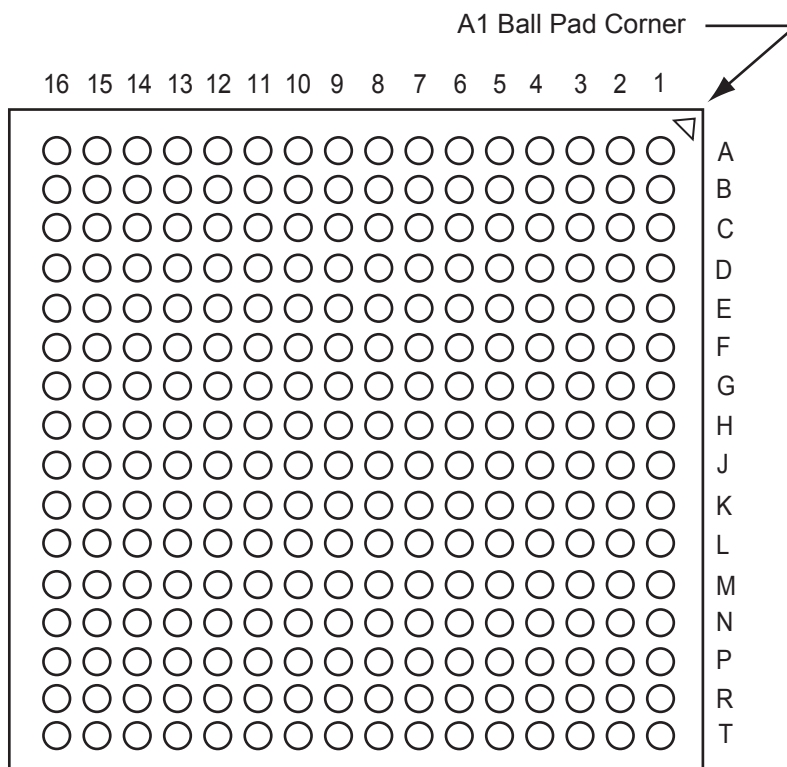
Table 3-10 • AFS250 Quiescent Supply Current Characteristics (continued)

Parameter	Description	Conditions	Temp.	Min	Typ	Max	Unit
IPP	Programming supply current	Non-programming mode, VPUMP = 3.63 V	T _J = 25°C		37	80	μA
			T _J = 85°C		37	80	μA
			T _J = 100°C		80	100	μA
		Standby mode ⁵ or Sleep mode ⁶ , VPUMP = 0 V			0	0	μA
ICCNVM	Embedded NVM current	Reset asserted, VCCNVM = 1.575 V	T _J = 25°C		10	40	μA
			T _J = 85°C		14	40	μA
			T _J = 100°C		14	40	μA
ICCPLL	1.5 V PLL quiescent current	Operational standby, VCCPLL = 1.575 V	T _J = 25°C		65	100	μA
			T _J = 85°C		65	100	μA
			T _J = 100°C		65	100	μA

Notes:

1. ICC is the 1.5 V power supplies, ICC, ICCPLL, ICC15A, ICCNVM.
2. ICC33A includes ICC33A, ICC33PMP, and ICCOSC.
3. ICCI includes all ICCI0, ICCI1, and ICCI2.
4. Operational standby is when the Fusion device is powered up, all blocks are used, no I/O is toggling, Voltage Regulator is loaded with 200 mA, VCC33PMP is ON, XTAL is ON, and ADC is ON.
5. XTAL is configured as high gain, VCC = VJTAG = VPUMP = 0 V.
6. Sleep Mode, VCC = VJTAG = VPUMP = 0 V.

FG256



Note

For Package Manufacturing and Environmental information, visit the Resource Center at <http://www.microsemi.com/soc/products/solutions/package/default.aspx>.

FG256				
Pin Number	AFS090 Function	AFS250 Function	AFS600 Function	AFS1500 Function
K9	VCC	VCC	VCC	VCC
K10	GND	GND	GND	GND
K11	NC	GDC2/IO57PPB1V0	GDC2/IO57PPB2V0	GDC2/IO84PPB2V0
K12	GND	GND	GND	GND
K13	NC	GDA0/IO54NDB1V0	GDA0/IO54NDB2V0	GDA0/IO81NDB2V0
K14	NC	GDA2/IO55PPB1V0	GDA2/IO55PPB2V0	GDA2/IO82PPB2V0
K15	VCCIB1	VCCIB1	VCCIB2	VCCIB2
K16	NC	GDB1/IO53PPB1V0	GDB1/IO53PPB2V0	GDB1/IO80PPB2V0
L1	NC	GEC1/IO63PDB3V0	GEC1/IO63PDB4V0	GEC1/IO90PDB4V0
L2	NC	GEC0/IO63NDB3V0	GEC0/IO63NDB4V0	GEC0/IO90NDB4V0
L3	NC	GEB1/IO62PDB3V0	GEB1/IO62PDB4V0	GEB1/IO89PDB4V0
L4	NC	GEB0/IO62NDB3V0	GEB0/IO62NDB4V0	GEB0/IO89NDB4V0
L5	NC	IO60NDB3V0	IO60NDB4V0	IO87NDB4V0
L6	NC	GEC2/IO60PDB3V0	GEC2/IO60PDB4V0	GEC2/IO87PDB4V0
L7	GNDA	GNDA	GNDA	GNDA
L8	AC0	AC0	AC2	AC2
L9	AV2	AV2	AV4	AV4
L10	AC3	AC3	AC5	AC5
L11	PTEM	PTEM	PTEM	PTEM
L12	TDO	TDO	TDO	TDO
L13	VJTAG	VJTAG	VJTAG	VJTAG
L14	NC	IO57NPB1V0	IO57NPB2V0	IO84NPB2V0
L15	GDB2/IO41PPB1V0	GDB2/IO56PPB1V0	GDB2/IO56PPB2V0	GDB2/IO83PPB2V0
L16	NC	IO55NPB1V0	IO55NPB2V0	IO82NPB2V0
M1	GND	GND	GND	GND
M2	NC	GEA1/IO61PDB3V0	GEA1/IO61PDB4V0	GEA1/IO88PDB4V0
M3	NC	GEA0/IO61NDB3V0	GEA0/IO61NDB4V0	GEA0/IO88NDB4V0
M4	VCCIB3	VCCIB3	VCCIB4	VCCIB4
M5	NC	IO58NPB3V0	IO58NPB4V0	IO85NPB4V0
M6	NC	NC	AV0	AV0
M7	NC	NC	AC1	AC1
M8	AG1	AG1	AG3	AG3
M9	AC2	AC2	AC4	AC4
M10	AC4	AC4	AC6	AC6
M11	NC	AG5	AG7	AG7
M12	VPUMP	VPUMP	VPUMP	VPUMP
M13	VCCIB1	VCCIB1	VCCIB2	VCCIB2
M14	TMS	TMS	TMS	TMS

5 – Datasheet Information

List of Changes

The following table lists critical changes that were made in each revision of the Fusion datasheet.

Revision	Changes	Page
Revision 6 (March 2014)	Note added for the discontinuance of QN108 and QN180 packages to the "Package I/Os: Single-/Double-Ended (Analog)" table and the "Temperature Grade Offerings" table (SAR 55113, PDN 1306).	II and IV
	Updated details about page programming time in the "Program Operation" section (SAR 49291).	2-46
	ADC_START changed to ADCSTART in the "ADC Operation" section (SAR 44104).	2-104
Revision 5 (January 2014)	Calibrated offset values (AFS090, AFS250) of the external temperature monitor in Table 2-49 • Analog Channel Specifications have been updated (SAR 51464).	2-117
	Specifications for the internal temperature monitor in Table 2-49 • Analog Channel Specifications have been updated (SAR 50870).	2-117
Revision 4 (January 2013)	The "Product Ordering Codes" section has been updated to mention "Y" as "Blank" mentioning "Device Does Not Include License to Implement IP Based on the Cryptography Research, Inc. (CRI) Patent Portfolio" (SAR 43177).	III
	The note in Table 2-12 • Fusion CCC/PLL Specification referring the reader to SmartGen was revised to refer instead to the online help associated with the core (SAR 42563).	2-28
	Table 2-49 • Analog Channel Specifications was modified to update the uncalibrated offset values (AFS250) of the external and internal temperature monitors (SAR 43134).	2-117
	In Table 2-57 • Prescaler Control Truth Table—AV (x = 0), AC (x = 1), and AT (x = 3), changed the column heading from 'Full-Scale Voltage' to 'Full Scale Voltage in 10-Bit Mode', and added and updated Notes as required (SAR 20812).	2-130
	The values for the Speed Grade (-1 and Std.) for FDDRIMAX (Table 2-180 • Input DDR Propagation Delays) and values for the Speed Grade (-2 and Std.) for FDDOMAX (Table 2-182 • Output DDR Propagation Delays) had been inadvertently interchanged. This has been rectified (SAR 38514).	2-220, 2-222
	Added description about what happens if a user connects VAREF to an external 3.3 V on their board to the "VAREF Analog Reference Voltage" section (SAR 35188).	2-225
	Added a note to Table 3-2 • Recommended Operating Conditions ¹ (SAR 43429): The programming temperature range supported is T _{ambient} = 0°C to 85°C.	3-3
	Added the Package Thermal details for AFS600-PQ208 and AFS250-PQ208 to Table 3-6 • Package Thermal Resistance (SAR 37816). Deleted the Die Size column from the table (SAR 43503).	3-7
	Libero Integrated Design Environment (IDE) was changed to Libero System-on-Chip (SoC) throughout the document (SAR 42495). Live at Power-Up (LAPU) has been replaced with 'Instant On'.	NA
Revision 3 (August 2012)	Microblade U1AFS250 and U1AFS1500 devices were added to the product tables.	I – IV
	A sentence pertaining to the analog I/Os was added to the "Specifying I/O States During Programming" section (SAR 34831).	1-9